TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM16GZ47, SM16JZ47, SM16GZ47A, SM16JZ47A

AC POWER CONTROL APPLICATIONS

• Repetitive Peak Off-State Voltage: VDRM = 400V, 600V

• R.M.S On-State Current: IT (RMS) = 16A

• High Commutating (dv / dt)

• Isolation Voltage: VISOL = 1500V AC

MAXIMUM RATINGS

CHARACTER	ISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak	SM16GZ47 SM16GZ47A	$V_{ m DRM}$	400	٧	
Off-State Voltage	SM16JZ47 SM16JZ47A	V DRM	600		
R.M.S On-State Currer (Full Sine Waveform To		I _{T (RMS)}	16	А	
Peak One Cycle Surge On-State Current (Non-Repetitive)		l	150 (50Hz)	Α	
		I _{TSM}	165 (60Hz)		
I ² t Limit Value		I ² t	112.5	A ² s	
Critical Rate of Rise of Current	On-State (Note 1)	di / dt	50	A / µs	
Peak Gate Power Dissi	pation	P_{GM}	5	W	
Average Gate Power D	issipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage		V_{GM}	10	V	
Peak Gate Current		I _{GM}	2	А	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature F	Range	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t	= 1 min.)	V _{ISOL}	1500	V	

1. T1
2. T2
3. GATE

JEDEC —

JEITA —

TOSHIBA 13-10H1A

Weight: 1.7 g (typ.)

10.3MAX.

Unit: mm

ø3.2 ± 0.2

Note 1: di / dt Test condition $V_{DRM} = 0.5 \times Rated$

 $I_{TM} \le 25A$ $t_{gw} \ge 10\mu s$ $t_{gr} \le 250ns$

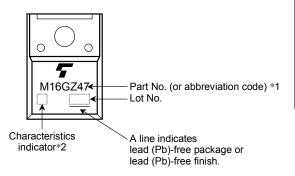
 $i_{GP} = I_{GT} \times 2.0$



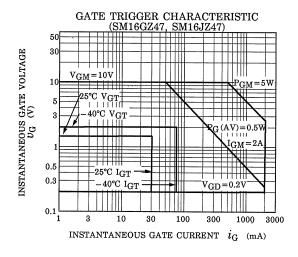
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

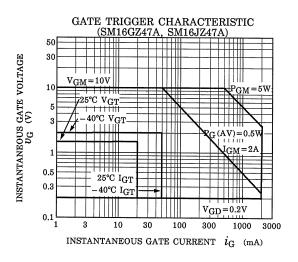
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} = Rated		_	_	20	μA		
Gate Trigger Voltage II		- 1	V _{GT}	$V_D = 12V$, $R_L = 20\Omega$	T2 (+) , Gate (+)		_	1.5	V	
		II			T2 (+) , Gate (-)	_	_	1.5		
		Ш			T2 (-) , Gate (-)		_	1.5		
		IV			T2 (-) , Gate (+)		_	_		
Gate Trigger Current SM16		I			T2 (+) , Gate (+)	_	_	30	-	
	SM16	M16GZ47			T2 (+) , Gate (-)	_	_	30		
	SM16	SJZ47	Ш		$V_D = 12V$, $R_L = 20\Omega$	T2 (-) , Gate (-)	_	_	30	mA
			IV			T2 (-) , Gate (+)	_	_	_	
		SM16GZ47A SM16JZ47A	I	l _{GT}		T2 (+) , Gate (+)	_	_	20	
	SM16		II			T2 (+) , Gate (-)	_	_	20	
	SM16		Ш			T2 (-) , Gate (-)	_	_	20	
		•				T2 (-) , Gate (+)	_	_	_	
Peak On-State Voltage		V _{TM}	I _{TM} = 25A		_	_	1.5	V		
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V		
Holding Current		I _H	V _D = 12V, I _{TM} = 1A		_	_	50	mA		
Thermal Resistance		R _{th (j-c)}	Junction to Case, AC			_	2.5	°C/W		
Critical Rate of Rise of Off-State Voltage	SM16GZ47 SM16JZ47		dv / dt	V _{DRM} = Rated, T _j = 125°C Exponential Rise		_	300	_	- V / µs	
	SM16GZ47 SM16JZ47		uv / ut			_	200	_		
Critical Rate of Rise of	SM16GZ47 SM16JZ47		(dv / dt) c	V _{DRM} = 400V, T _j = 125°C (di / dt) c = - 8.7A / ms		10	_	_	- V / μs	
		SM16GZ47 SM16JZ47				(uv / ut) C	4	_		_

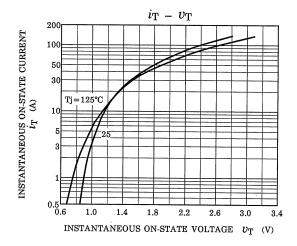
MARKING

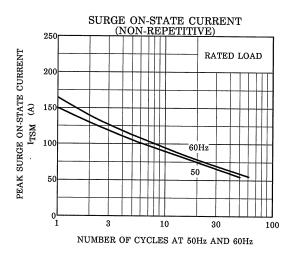


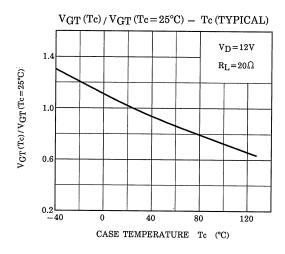
	Part No. (or abbreviation code)	Part No.
*1	M16GZ47	SM16GZ47, SM16GZ47A
	M16JZ47	SM16JZ47, SM16JZ47A
*2	Nothing	SM16GZ47, SM16JZ47
	A	SM16GZ47A, SM16JZ47A

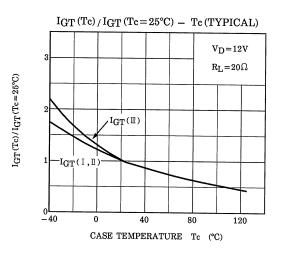


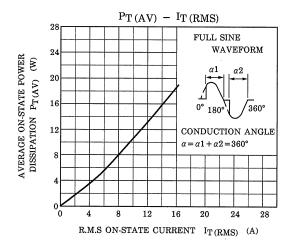


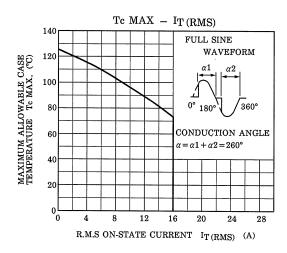


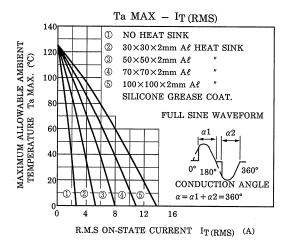


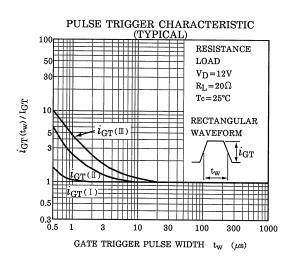


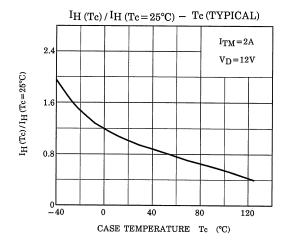


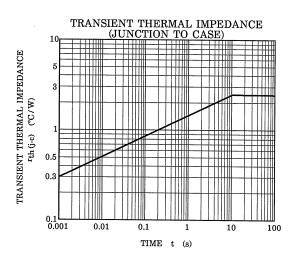












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